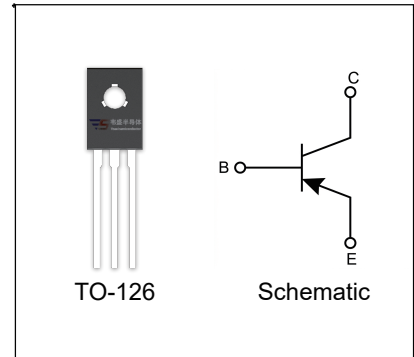


BD234 / BD236 / BD238 TRANSISTOR (PNP)

FEATURES

- Complement to BD233/BD235/BD237 respectively



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{CBO}	Collector-Base Voltage	BD234	-45	V
		BD236	-60	
		BD238	-100	
V_{CEO}	Collector-Emitter Voltage	BD234	-45	V
		BD236	-60	
		BD238	-80	
V_{EB0}	Emitter-Base Voltage		-5	V
I_C	Collector Current –Continuous		-2	A
P_C	Collector Dissipation		1.25	W
P_C	Collector Dissipation (T _c =25°C)		25	W
R_{ΘJA}	Thermal Resistance from Junction to Ambient		100	°C/W
R_{ΘJC}	Thermal Resistance from Junction to Case		5	°C/W
T_J, T_{stg}	Operation Junction and Storage Temperature Range		-55~+150	°C

T_a=25 °C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage BD234 BD236 BD238	$V_{(BR)CBO}$	$I_C=-1mA, I_E=0$	-45 -60 -100		V
Collector-emitter breakdown voltage BD234 BD236 BD238	$V_{(BR)CEO}$	$I_C=-100mA, I_B=0$	-45 -60 -80		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-5		V
Collector cut-off current BD234 BD236 BD238	I_{CBO}	$V_{CB}=-45V, I_E=0$ $V_{CB}=-60V, I_E=0$ $V_{CB}=-100V, I_E=0$		-100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-1	mA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2V, I_C=-150mA$	40		
	$h_{FE(2)}$	$V_{CE}=-2V, I_C=-1A$	25		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-1A, I_B=-100mA$		-0.6	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-250mA,$ $f=10MHz$	3		MHz

